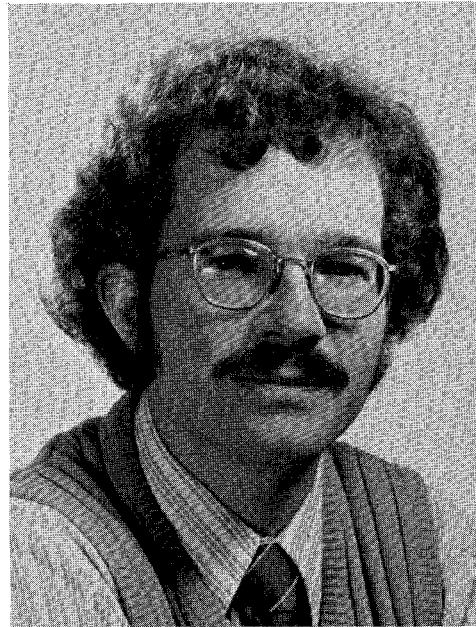


1978 MTT-S MICROWAVE APPLICATION AWARD

TO

STEPHEN I. LONG

For "The Study of InP Materials, Devices and Circuits for Applications to Millimeter-Wave Gunn Diode Devices."



Stephen I. Long was born in Alameda, California on January 11, 1946. He received the B.S. degree in engineering physics from the University of California, Berkeley in 1967 and the M.S. and Ph.D. degrees in electrical engineering from Cornell University, Ithaca, N.Y. in 1969 and 1974 respectively. His thesis research dealt with steady state liquid phase epitaxial growth of GaAs.

During 1966 and 1967, he was a staff assistant at Stanford Linear Accelerator Center and investigated electron multiplication effects in alkali halides. During 1968 and 1969, he helped to develop GaAs liquid phase epitaxial growth systems at Cayuga Associates, Ithaca, N.Y. for transferred electron device fabrication. From 1969 to 1973, he served as a project engineer at the Rome Air Development Center, Griffiss AFB, N.Y. where he investigated and developed a steady state LPE growth technique for thick, uniformly doped layers. In 1974, he joined Varian Associates, Palo Alto, California where he has worked on vapor phase epitaxial growth of GaAs and InP, development of GaAs and InP, development of GaAs high efficiency IMPATT devices and millimeter wave InP oscillator and amplifier devices. He is presently manager of the semiconductor engineering group, solid state west division.

Dr. Long is a member of IEEE, Tau Beta Pi, and the Northern California Crystal Growers.

Steve wishes to share the honor with his colleagues by acknowledging their key contributions to the development of InP devices: They are R.D. Fairman for InP epitaxial material growth; R.J. Hamilton, Jr., for circuit design and device evaluation; J.T. Andrews for device evaluation; and F.B. Fank for his leadership, encouragement, and support.